

What Is Claimed Is:

1. A high frequency circuit module provided with a two- or more-layer dielectric substrate, a semiconductor element and matching circuits on the input side and on the output side respectively of the semiconductor element respectively formed on the dielectric substrate, and ground metal, wherein: a thickness of the dielectric substrate between a conductor of conductor line of said matching circuit on the output side and said ground metal is composed of two or more layers.

2. A high frequency circuit module according to Claim 1, wherein:

a thickness of the dielectric substrate between said conductor of conductor line of said matching circuit on the input side and said ground metal is composed of two or more layers.

3. A high frequency circuit module provided with a two- or more-layer dielectric substrate, a semiconductor element and matching circuits on the input side and on the output side respectively of the semiconductor element respectively formed on the dielectric substrate, and ground metal, wherein:

ground metal provided to the dielectric substrate existing between a conductor of transmission line of said matching circuit on the output side and said ground metal is formed in the shape in which a part is hollowed out so that a part opposite to said

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conductor transmission line is included.

4. A high frequency circuit module according to Claim 3, wherein:

5 ground metal provided to the dielectric substrate existing between said conductor of transmission line of said matching circuit on the input side and said ground metal is formed in the shape in which a part is hollowed out so that a part opposite to said conductor of said transmission line is included.

10 5. A high frequency circuit module provided with a two- or more-layer dielectric substrate, a semiconductor element and matching circuits on the input side and on the output side respectively of the semiconductor element respectively formed on the dielectric substrate, and ground metal, wherein:

15 a thickness of the dielectric substrate between a conductor of transmission line of said matching circuit on the input side and said ground metal is composed of two or more layers.

20 6. A high frequency circuit module according to Claim 5, wherein:

25 a thickness of the dielectric substrate between said conductor of transmission line of said matching circuit on the output side and said ground metal is composed of two or more layers.

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A high frequency circuit module provided with a two- or more-layer dielectric substrate, a semiconductor element and matching circuits on the

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input side and on the output side respectively of the semiconductor element respectively formed on the dielectric substrate, and ground metal, wherein:

5 ground metal provided to the dielectric substrate existing between a conductor of transmission line of said matching circuit on the input side and said ground metal is formed in the shape in which a part is hollowed out so that a part opposite to said conductor of transmission line is included.

10 8. A high frequency circuit module according to Claim 7, wherein:

15 ground metal provided to the dielectric substrate existing between said conductor of transmission line of said matching circuit on the output side and said ground metal is formed in the shape in which a part is hollowed out so that a part opposite to conductor of said transmission line is included.

20 9. A communication device, wherein:
the high frequency circuit module according to Claim 1 is used for a power amplifier at the transmitting end.

25 10. A communication device, wherein:
the high frequency circuit module according to Claim 2 is used for the power amplifier at the transmitting end.

11. A communication device, wherein:
the high frequency circuit module according to

Claim 3 is used for the power amplifier at the transmitting end.

12. A communication device, wherein:
the high frequency circuit module according to
5 Claim 4 is used for the power amplifier at the transmitting end.

13. A communication device, wherein:
the high frequency circuit module according to
10 Claim 5 is used for a low noise amplifier at the receiving end.

14. A communication device, wherein:
the high frequency circuit module according to
Claim 6 is used for the low noise amplifier at the receiving end.

15. A communication device, wherein:
the high frequency circuit module according to
Claim 7 is used for the low noise amplifier at the receiving end.

16. A communication device, wherein:
20 the high frequency circuit module according to
Claim 8 is used for the low noise amplifier at the receiving end.

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